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THIS SPEC IS OBSOLETE

Spec No: 38-05255

Spec Title: CY7C1069AV33, 2M X 8 STATIC RAM

Replaced by: None





Features

- High speed
 □ t_{AA} = 10 ns
- Low active power ☐ 990 mW (max)
- Operating voltages of 3.3 ± 0.3 V
- 2.0 V data retention
- Automatic power down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with \overline{CE}_1 and CE_2 features
- Available in Pb-free 54-pin thin small outline package (TSOP) II package

Functional Description

The CY7C1069AV33 is a high performance complementary metal oxide semiconductor (CMOS) static RAM organized as 2,097,152 words by 8 bits. Writing to the device is accomplished by enabling the chip (by taking $\overline{\text{CE}}_1$ LOW and $\overline{\text{CE}}_2$ HIGH) and Write Enable (WE) inputs LOW.

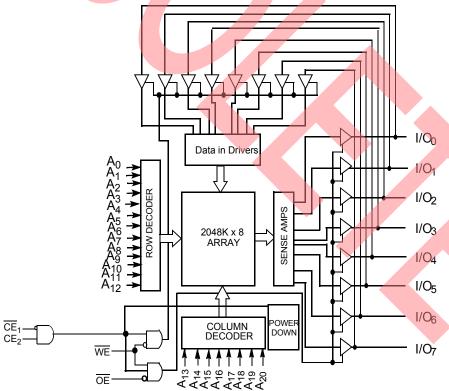
Reading from the device is accomplished by enabling the chip $(\overline{CE}_1 \text{ LOW})$ and $(\overline{CE}_1 \text{ LOW})$ and $(\overline{CE}_1 \text{ LOW})$ as well as forcing the Output Enable (\overline{OE}) LOW while forcing the WE HIGH. See Truth Table on page 9 for a complete description of Read and Write modes.

The input/output pins (I/O $_0$ through I/O $_1$) are placed in a high impedance state when the device is deselected (CE $_1$ HIGH or CE $_2$ LOW), the outputs are disabled (OE HIGH), or during a Write operation (CE $_1$ LOW, CE $_2$ HIGH, and WE LOW).

The CY7C1069AV33 is available in a 54-pin TSOP II package with center power and ground (revolutionary) pinout.

For a complete list of related documentation, click here.

Logic Block Diagram





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Selection Guide

Description	-10	Unit
Maximum access time	10	ns
Maximum operating current	275	mA
Maximum CMOS standby current	50	mA

Pin Configuration

Figure 1. 54-pin TSOP II pinout [1, 2]



Notes

- 1. NC pins are not connected on the die.
- 2. $\mbox{DN}\dot{\mbox{U}}$ pins have to be left floating or tied to $\mbox{V}_{\mbox{SS}}$ to ensure proper application.



Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature—65 °C to +150 °C Ambient temperature

with power applied –55 °C to +125 °C

Supply voltage on V_{CC} to relative GND $^{[3]}$ -0.5 V to +4.6 V

DC voltage applied to output	S
in high Z state [3]	s 0.5 V to V _{CC} + 0.5 V
DC input voltage [3]	0.5 V to V _{CC} + 0.5 V
Current into outputs (LOW)	20 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0 °C to +70 °C	$3.3~V\pm0.3~V$
Industrial	–40 °C to +85 °C	

DC Electrical Characteristics

Over the Operating Range

Doromotor	Description	Test Conditions	-1	Unit	
Parameter	Description	rest Conditions	Min	Max	Unit
V _{OH}	Output HIGH voltage	$V_{CC} = Min, I_{OH} = -4.0 \text{ mA}$	2.4	-	V
V_{OL}	Output LOW voltage	$V_{CC} = Min, I_{OL} = 8.0 \text{ mA}$	-	0.4	V
V _{IH}	Input HIGH voltage		2.0	V _{CC} + 0.3	V
V_{IL}	Input LOW voltage [3]		-0.3	0.8	V
I _{IX}	Input leakage current	$GND \le V_I \le V_{CC}$	-1	+1	μΑ
I _{OZ}	Output leakage current	$GND \le V_{OUT} \le V_{CC}$, Output Disabled	-1	+1	μΑ
I _{CC}	V _{CC} Operating supply current	$V_{CC} = Max$, $f = f_{MAX} = 1/t_{RC}$	-	275	mA
I _{SB1}	Automatic CE power down current – TTL Inputs	$CE_2 \le V_{IL}$, Max V_{CC} , $\overline{CE}_1 \ge V_{IH}$, $V_{IN} \ge V_{IH}$ or $V_{IN} \le V_{IL}$, $f = f_{MAX}$	_	70	mA
I _{SB2}	Automatic CE power down current – CMOS inputs	$CE_2 \le 0.3 \text{ V, Max V}_{CC},$ $\overline{CE}_1 \ge V_{CC} - 0.3 \text{ V,}$ $V_{IN} \ge V_{CC} - 0.3 \text{ V or V}_{IN} \le 0.3 \text{ V, f} = 0$	-	50	mA



^{3.} V_{IL} (min.) = -2.0 V for pulse durations of less than 20 ns.

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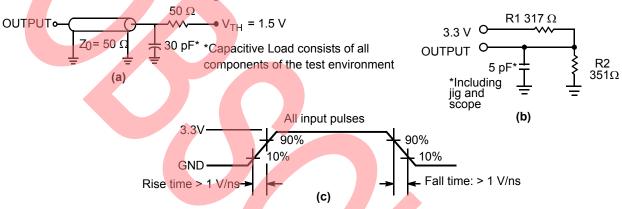


Capacitance

Parameter [4]	Description	Test Conditions	TSOP II	Unit
C _{IN}	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = 3.3 \text{V}$	6	pF
C _{OUT}	I/O capacitance		8	pF

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms [5]



Data Retention Waveform

Figure 3. Data Retention Waveform



Notes

- 4. Tested initially and after any design or process changes that may affect these parameters.
- Valid SRAM operation does not occur until the power supplies have reached the minimum operating V_{DD} (3.0V). As soon as 1ms (T_{power}) after reaching the minimum operating V_{DD}, normal SRAM operation can begin including reduction in V_{DD} to the data retention (V_{CCDR}, 2.0V) voltage.



AC Switching Characteristics

Over the Operating Range

Parameter [6]	Description	-1	10	11!4
Parameter [2]	Description	Min	Max	Unit
Read Cycle			•	
t _{power}	V _{CC} (typical) to the first access ^[7]	1	_	ms
t _{RC}	Read cycle time	10	_	ns
t _{AA}	Address to data valid	-	10	ns
t _{OHA}	Data hold from address change	3	_	ns
t _{ACE}	CE ₁ LOW/CE ₂ HIGH to data valid	_	10	ns
t _{DOE}	OE LOW to data valid	_	5	ns
t _{LZOE}	OE LOW to low Z [8]	1	_	ns
t _{HZOE}	OE HIGH to high Z [8]	-	5	ns
t _{LZCE}	CE ₁ LOW/CE ₂ HIGH to low Z [8]	3	_	ns
t _{HZCE}	CE ₁ HIGH/CE ₂ LOW to high Z [8]	-	5	ns
t _{PU}	CE ₁ LOW/CE ₂ HIGH to power up [9]	0	_	ns
t _{PD}	CE ₁ HIGH/CE ₂ LOW to power down [9]	-	10	ns
Write Cycle [9,	10]			
t _{WC}	Write cycle time	10	_	ns
t _{SCE}	CE ₁ LOW/CE ₂ HIGH to write end	7	_	ns
t _{AW}	Address setup to write end	7	_	ns
t _{HA}	Address hold from write end	0	_	ns
t _{SA}	Address setup to write start	0	_	ns
t _{PWE}	WE pulse width	7	_	ns
t _{SD}	Data setup to write end	5.5	_	ns
t _{HD}	Data hold from write end	0	_	ns
t _{LZWE}	WE HIGH to low Z [8]	3		ns
t _{HZWE}	WE LOW to high Z [8]		5	ns

Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and transmission line loads. Test conditions for the Read cycle use output loading shown in part a) of the AC test loads, unless specified otherwise.
 This part has a voltage regulator which steps down the voltage from 3V to 2V internally. t_{power} time has to be provided initially before a Read/Write operation is started.
 t_{HZOE}, t_{HZCE}, t_{HZWE} and t_{LZOE}, t_{LZCE}, and t_{LZWE} are specified with a load capacitance of 5 pF as in (b) of AC Test Loads. Transition is measured ±200 mV from steady-state voltage.
 These parameters are guaranteed by design and are not tested.
 The internal Write time of the memory is defined by the overlap of CE₁ LOW/CE₂ HIGH, and WE LOW. CE₁ and WE must be LOW along with CE₂ HIGH to initiate a Write, and the transition of any of these signals can terminate the Write. The input data setup and hold timing should be referenced to the leading edge of the signal that terminates the Write. that terminates the Write.



Switching Waveforms

Figure 4. Read Cycle No. 1 [11, 12]

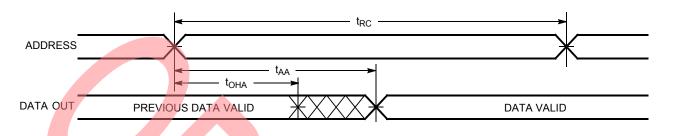
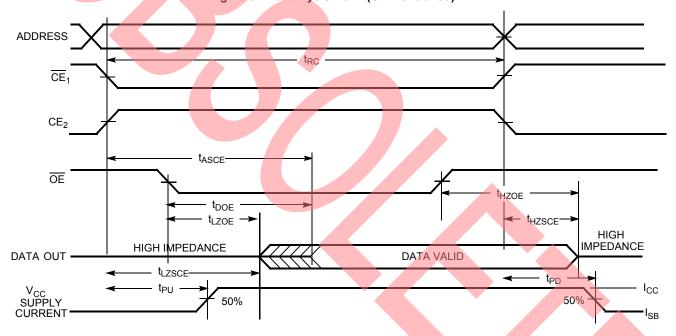


Figure 5. Read Cycle No. 2 (OE Controlled) [12, 13]



Notes
11. Device is continuously selected. $\overline{CE}_1 = V_{IL}$, $CE_2 = V_{IH}$.
12. WE is HIGH for Read cycle.
13. Address valid prior to or coincident with \overline{CE}_1 transition LOW and CE_2 transition HIGH.



Switching Waveforms (continued)

Figure 6. Write Cycle No. 1 ($\overline{\text{CE}}_1$ Controlled) [14, 15, 16]

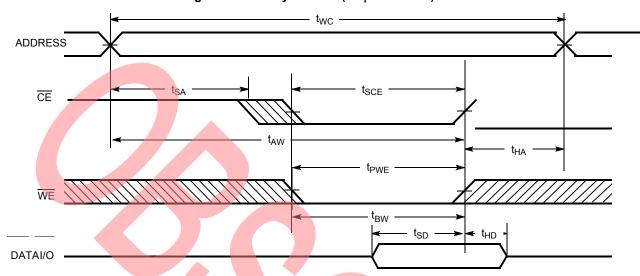
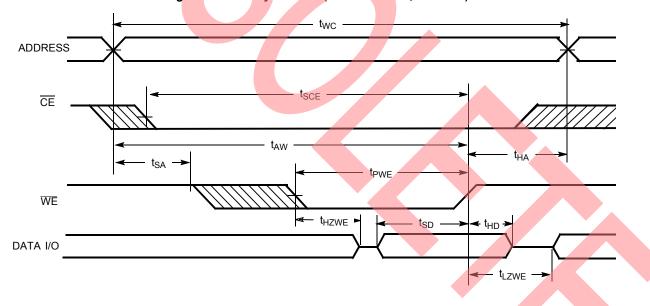


Figure 7. Write Cycle No. 2 (WE Controlled, OE LOW) [14, 15, 16]



^{14.} Data I/O is high-impedance if $\overline{\text{OE}}$ = V_{IH}.

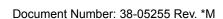
15. If $\overline{\text{CE}}_1$ goes HIGH/CE₂ LOW simultaneou<u>sly</u> with $\overline{\text{WE}}$ going HIGH, the output remains in a high–impedance state.

16. $\overline{\text{CE}}$ above is defined as a combination of $\overline{\text{CE}}_1$ and $\overline{\text{CE}}_2$. It is active low.



Truth Table

CE ₁	CE ₂	OE	WE	I/O ₀ –I/O ₇	Mode	Power
Н	X	Х	Х	High Z	Power down	Standby (I _{SB})
Х	L	Х	X	High Z	Power down	Standby (I _{SB})
L	Н	L	Н	Data Out	Read all bits	Active (I _{CC})
L	Н	X	L	Data In	Write all bits	Active (I _{CC})
L	Н	Н	Н	High Z	Selected, outputs disabled	Active (I _{CC})

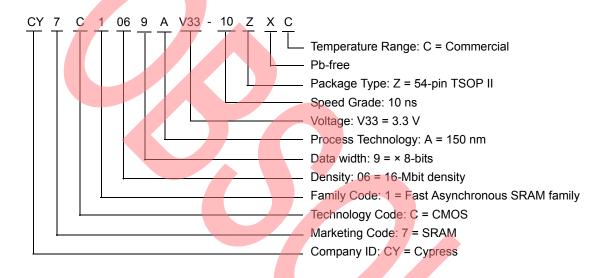




Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1069AV33-10ZXC	51-85160	54-pin TSOP II (Pb-free)	Commercial

Ordering Code Definitions

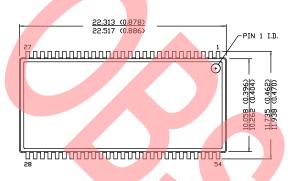


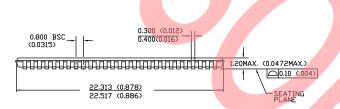


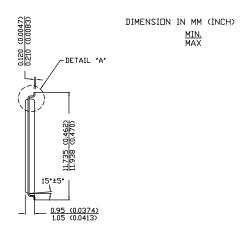
Package Diagram

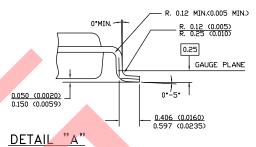
Figure 8. 54-pin TSOP II (22.4 × 11.84 × 1.0 mm) Package Outline, 51-85160

54 Lead TSOP TYPE II - STANDARD









51-85160 *E



Acronyms

Acronym	Description		
CE	Chip Enable		
CMOS	Complementary Metal Oxide Semiconductor		
I/O	Input/Output		
OE	Output Enable		
SRAM	Static Random Access Memory		
TSOP	Thin Small Outline Package		
TTL	Transistor-Transistor Logic		
WE	Write Enable		

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
mA	milliampere
ms	millisecond
mV	millivolt
mW	milliwatt
ns	nanosecond
%	percent
pF	picofarad
V	volt
W	watt



Document History Page

ocument Title: CY7C1069AV33, 2M × 8 Static RAM ocument Number: 38-05255				
Rev.	ECN No.	Submission Date	Orig. of Change	Description of Change
**	113724	03/27/02	NSL	New data sheet
*A	117060	07/31/02	DFP	Removed 15-ns bin
*B	117990	08/30/02	DFP	Added 8-ns bin Changing I_{CC} for 8, 10, 12 bins t_{power} changed from 1 μ s to 1 ms Load Cap Comment changed (for Tx line load) t_{SD} changed to 5.5 ns for the 10-ns bin Changed some 8-ns bin #s (t_{HZ} , t_{DOE} , t_{DBE}) Removed hz < Iz comments
*C	120385	11/13/02	DFP	Final data sheet Added note 4 to "AC Test Loads and Waveforms" and note 7 to t _{pu} and t _{pd} Updated Input/Output Caps (for 48-ball BGA only) to 8 pF/10 pF and for th 54-pin TSOP to 6/8 pF
*D	124441	2/25/03	MEG	Changed I _{SB1} from 100 mA to 70 mA Shaded the 48-ball FBGA product offering information
*E	403984	See ECN	NXR	Changed the Logic Block Diagram On page # 1 Added notes under Pin Configuration Changed the Package diagram of 51-85162 from Rev *A to Rev *D Changed 48-ball FBGA to 60-ball FBGA in Pin Configuration Updated the Ordering Information
*F	492137	See ECN	NXR	Removed 8 ns speed bin from product offering Changed the description of I _{IX} from Input Load Current to Input Leakage Current in DC Electrical Characteristics table Updated the Ordering Information
*G	2784946	10/12/2009	VKN / PYRS	Updated template Corrected typo in footnote 9 Updated Ordering Information table
*H	2897049	03/25/10	AJU	Removed inactive parts from the ordering information table. Updated package diagrams.
*	2950666	06/11/2010	VKN	Removed 12 ns speed bin, Removed 60-ball FBGA package Updated Ordering Information: Updated part numbers. Added Ordering Code Definitions. Added Acronyms.
*J	3096933	11/29/2010	PRAS	Added Units of Measure. Minor edits. Updated to new template.
*K	4214675	12/09/2013	VINI	Updated Package Diagram: spec 51-85160 – Changed revision from *A to *D. Updated to new template. Completing Sunset Review.
*L	4574377	11/19/2014	VINI	Updated Functional Description: Added "For a complete list of related documentation, click here." at the en Updated Package Diagram: spec 51-85160 – Changed revision from *D to *E.
*M	5574052	01/04/2017	VINI	Obsolete document. Completing Sunset Review.



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